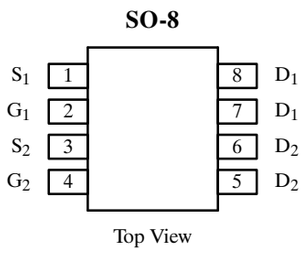
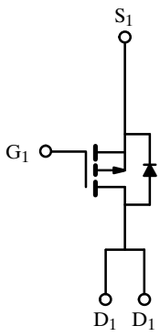
Si4953DY

Dual P-Channel Enhancement-Mode MOSFET

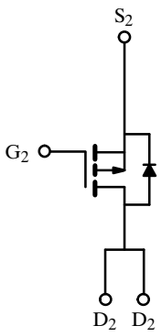
Product Summary

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
−30	0.053 @ V_{GS} = −10 V	±4.9
	0.095 @ V_{GS} = −4.5 V	±3.6





P-Channel MOSFET



P-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	−30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	±4.9	A
	T_A = 70°C		±3.9	
Pulsed Drain Current		I_{DM}	±30	
Continuous Source Current (Diode Conduction)[a]		I_S	−1.7	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.0	W
	T_A = 70°C		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to 150	°C

Thermal Resistance Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient[a]	R_{thJA}	62.5	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

Subsequent updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #1235.

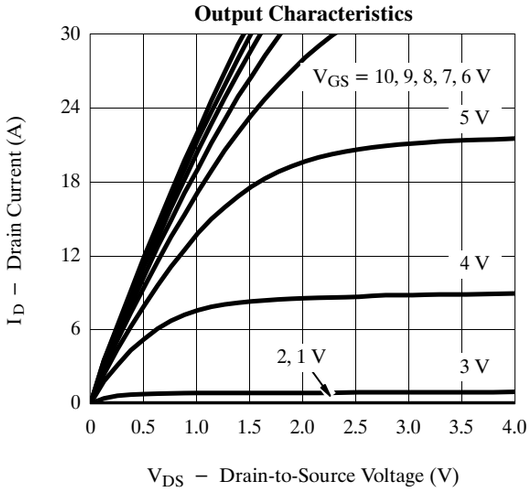
Specifications (T_J = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = −250 µA	−1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = −30 V, V_{GS} = 0 V			−1	µA
		V_{DS} = −30 V, V_{GS} = 0 V, T_J = 55°C			−25	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} ≤ −5 V, V_{GS} = −10 V	−20			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = −10 V, I_D = −4.9 A		0.043	0.053	Ω
		V_{GS} = −4.5 V, I_D = −3.6 A		0.070	0.095	
Forward Transconductance[b]	g_{fs}	V_{DS} = −15 V, I_D = −4.9 A		10		S
Diode Forward Voltage[b]	V_{SD}	I_S = −1.7 A, V_{GS} = 0 V		0.8	−1.2	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = −15 V, V_{GS} = −10 V, I_D = −4.9 A		16	25	nC
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}			2		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = −15 V, R_L = 15 Ω I_D ≅ −1 A, V_{GEN} = −10 V, R_G = 6 Ω		9	15	ns
Rise Time	t_r			13	20	
Turn-Off Delay Time	$t_{d(off)}$			25	40	
Fall Time	t_f			15	25	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = −1.7 A, di/dt = 100 A/µs		60	90	

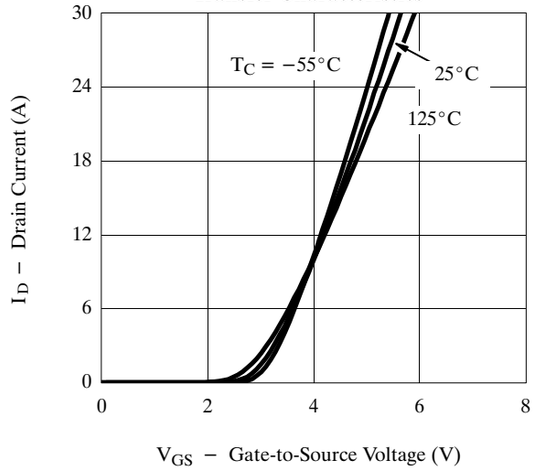
Notes
a. For design aid only; not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.

Typical Characteristics (25°C Unless Noted)

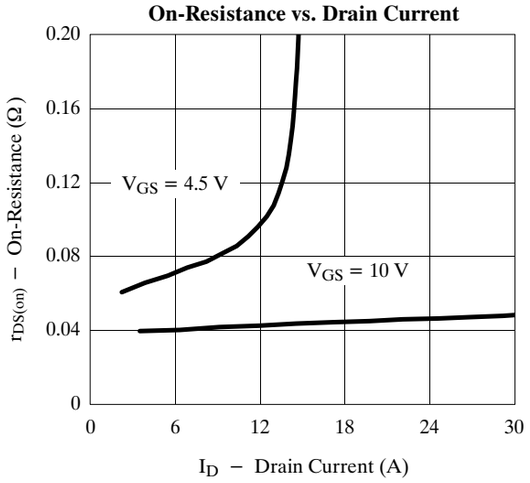
Output Characteristics



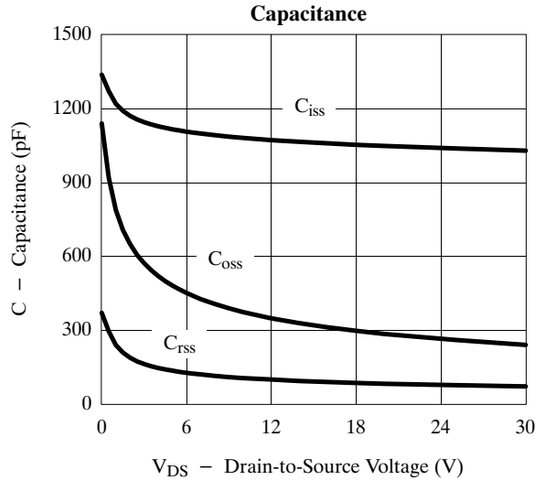
Transfer Characteristics



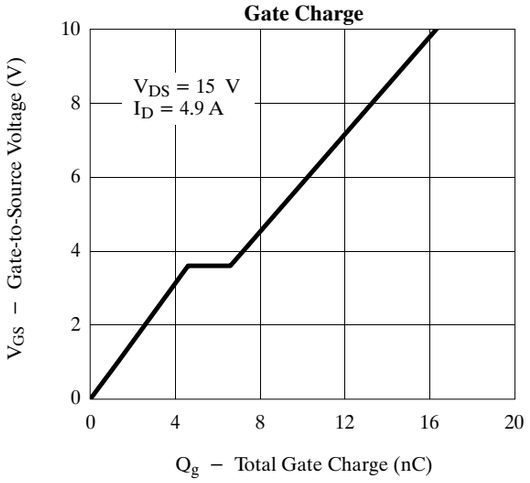
On-Resistance vs. Drain Current



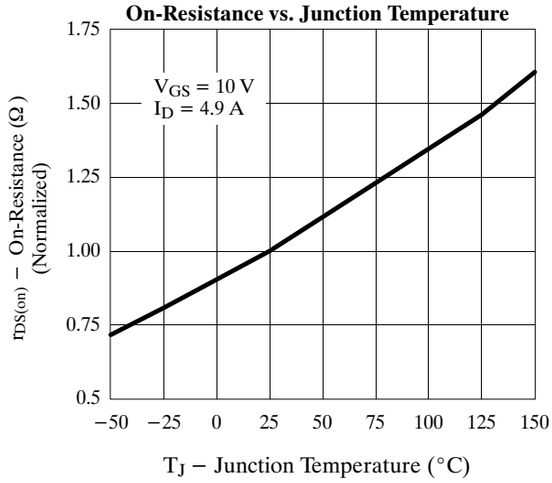
Capacitance



Gate Charge



On-Resistance vs. Junction Temperature



Typical Characteristics (25°C Unless Noted)